

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2022/0385285 A1 **ODA**

(43) Pub. Date: Dec. 1, 2022

(54) POWER SEMICONDUCTOR DEVICE

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Appl. No.: 17/682,227 (21)

(22)Filed: Feb. 28, 2022

(30)Foreign Application Priority Data

May 31, 2021 (JP) 2021-091366

Publication Classification

(51) **Int. Cl.**

H03K 17/567 (2006.01)H02M 1/088 (2006.01)H02M 1/00 (2006.01) (52) U.S. Cl.

CPC H03K 17/567 (2013.01); H02M 1/088 (2013.01); H02M 1/0006 (2021.05)

(57)ABSTRACT

A power semiconductor device of the present disclosure includes: a first switching element; a second switching element connected in parallel to the first switching element, and having a higher short circuit capability than the first switching element; drive circuits to drive the first switching element and the second switching element; and determination circuits to compare a target current as a sum of a current flowing through the first switching element and a current flowing through the second switching element to a first threshold and a second threshold greater than the first threshold. The drive circuits switch off the first switching element when the determination circuits determine that the target current is equal to or greater than the first threshold, and switch off the second switching element when the determination circuits determine that the target current is equal to or greater than the second threshold.

